

FUJI POWER MOSFET Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

Features

- High speed switching
- Low on-resistance
- No secondary breakdown
- Low driving power
- Avalanche-proof

Applications

- Switching regulators
- UPS (Uninterruptible Power Supply)
- DC-DC converters

Maximum ratings and characteristic Absolute maximum ratings

($T_c=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V_{DS}	100	V
	V_{DSX}^{*5}	70	V
Continuous drain current	I_D	± 29	A
Pulsed drain current	$I_{D(puls)}$	± 116	A
Gate-source voltage	V_{GS}	± 30	V
Non-repetitive Avalanche current	I_{AS}^{*2}	29	A
Maximum Avalanche Energy	E_{AS}^{*1}	155.8	mJ
Maximum Drain-Source dV/dt	dV_{DS}/dt^{*4}	20	kV/ μs
Peak Diode Recovery dV/dt	dV/dt^{*3}	5	kV/ μs
Max. power dissipation	P_D	$T_a=25^\circ\text{C}$	2.16
		$T_c=25^\circ\text{C}$	37
Operating and storage temperature range	T_{ch}	+150	$^\circ\text{C}$
	T_{stg}	-55 to +150	$^\circ\text{C}$
Isolation voltage	V_{ISO}^{*6}	2	kVrms

*1 $L=222\mu\text{H}$, $V_{CC}=48\text{V}$, $T_{ch}=25^\circ\text{C}$, See to Avalanche Energy Graph *2 $T_{ch} \leq 150^\circ\text{C}$

*3 $I_F \leq -I_D$, $-di/dt=50\text{A}/\mu\text{s}$, $V_{CC} \leq BV_{DSS}$, $T_{ch} \leq 150^\circ\text{C}$ *4 $V_{DS} \leq 100\text{V}$ *5 $V_{GS} = -30\text{V}$ *6 $t=60\text{sec}$ $f=60\text{Hz}$

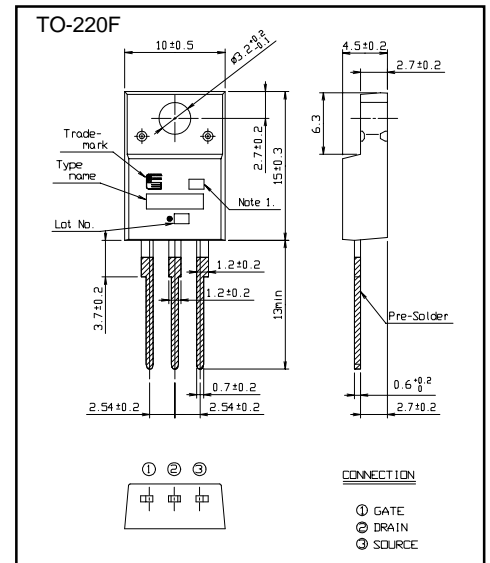
Electrical characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$ $V_{GS} = 0\text{V}$	100			V
Gate threshold voltage	$V_{GS(th)}$	$I_D = 250\mu\text{A}$ $V_{DS} = V_{GS}$	3.0		5.0	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100\text{V}$ $V_{GS} = 0\text{V}$			25	μA
		$V_{DS} = 80\text{V}$ $V_{GS} = 0\text{V}$			250	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 30\text{V}$ $V_{DS} = 0\text{V}$		10	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 10\text{A}$ $V_{GS} = 10\text{V}$		47	62	$\text{m}\Omega$
Forward transconductance	g_{fs}	$I_D = 10\text{A}$ $V_{DS} = 25\text{V}$	6	12		S
Input capacitance	C_{iss}	$V_{DS} = 75\text{V}$		730	1095	pF
Output capacitance	C_{oss}	$V_{GS} = 0\text{V}$		190	285	pF
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$		12	18	pF
Turn-on time t_{on}	$t_{d(on)}$	$V_{CC} = 48\text{V}$ $I_D = 10\text{A}$		12	18	ns
	t_r	$V_{GS} = 10\text{V}$		3.8	6	
Turn-off time t_{off}	$t_{d(off)}$	$R_{GS} = 10\Omega$		23	35	ns
	t_f			8.5	13	
Total Gate Charge	Q_G	$V_{CC} = 50\text{V}$		22	33	nC
Gate-Source Charge	Q_{GS}	$I_D = 20\text{A}$		9	13.5	
Gate-Drain Charge	Q_{GD}	$V_{GS} = 10\text{V}$		6	9	
Avalanche capability	I_{AV}	$L = 222\mu\text{H}$ $T_{ch} = 25^\circ\text{C}$	29			A
Diode forward on-voltage	V_{SD}	$I_F = 20\text{A}$ $V_{GS} = 0\text{V}$ $T_{ch} = 25^\circ\text{C}$		1.10	1.65	V
Reverse recovery time	t_{rr}	$I_F = 20\text{A}$ $V_{GS} = 0\text{V}$		65		ns
Reverse recovery charge	Q_{rr}	$-di/dt = 100\text{A}/\mu\text{s}$ $T_{ch} = 25^\circ\text{C}$		0.17		μC

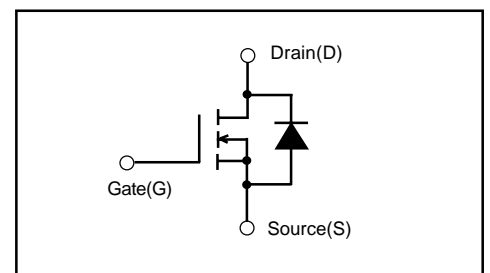
Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(ch-c)}$	channel to case			3.378	$^\circ\text{C}/\text{W}$
	$R_{th(ch-a)}$	channel to ambient			58.0	$^\circ\text{C}/\text{W}$

Outline Drawings (mm)



Equivalent circuit schematic



Characteristics

